

MBR20V45CTH/FCTH

Trench MOS Barrier Schottky Rectifier - 20Amp 45Volt

Features

- -Plastic package has Underwriters Laboratory Flammability Classifications 94V-0
- -High Junction Temperature Capability
- -Low forward voltage, high current capability
- -High surge capacity
- -Low power loss, high efficiency
- -Halogen-Free

Application

-AC/DC Switching Adaptor and other Switching Power Supply

☐ Absolute maximum ratings

Symbol	Ratings	Unit	Conditions	
I F(AV)	20	А	Average Forward Current	
VRRM	45	V	Repetitive Peak Reverse Voltage	
IFSM	150	Α	Peak Forward Surge Current	
VF	0.46	V	Forward Voltage Drop	
Tj, Tstg	-65 to +150	°C	Operating and Storage Temperature	

Electrical characteristics

Parameters	Parameters Symbol Ratings		ings	Conditions	
	VF	TYP.	MAX.	Per Leg at IF = 10A	
Instantaneous Forward Voltage		0.49V	0.52V	Tc = 25°C	
		0.46V	0.49V	Tc = 125°C	
	lr	TYP.	MAX.	Per Leg at VR = 45V	
Reverse Leakage Current		0.2mA	0.5mA	Tc = 25°C	
		25mA	50mA	Tc = 125°C	
		2.2 °C/W		Per Leg	
Typical Thermal Resistance, Junction to Case	Rθ (j-c)			TO-220AB	
		4.5 °C/W		ITO-220AB	

Note: 1.Mounted on P.C.B with copper pad size 20mm x 30mm, thickness 1.5mm

December 2018 / Rev.7.2

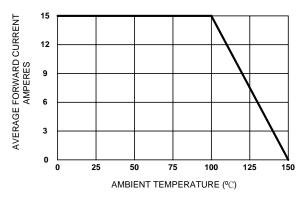
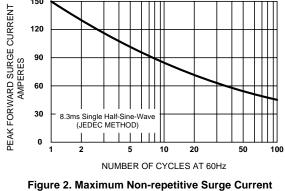


Figure 1. Forward Current Derating Curve



150

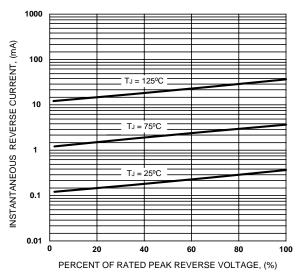


Figure 3. Typical Reverse Characteristics

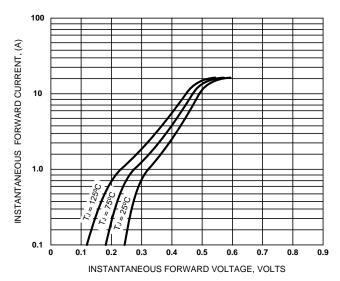


Figure 4. Typical Forward Characteristics

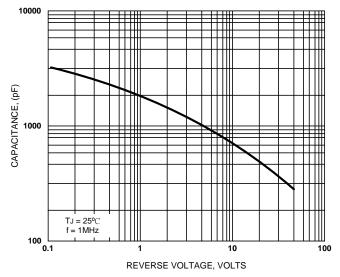
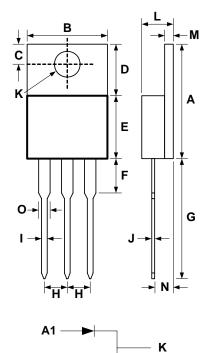


Figure 5. Typical Junction Capacitance

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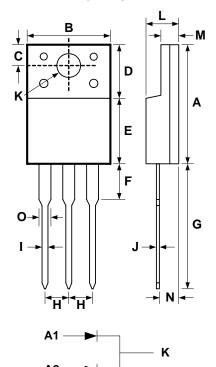
TO-220AB



DIMENSIONS					
DIM	INCHES		MILLIMETERS		NOTE
	MIN	MAX	MIN	MAX	NOTE
Α	.590	.630	15.0	16.00	
В	.390	.413	9.90	10.50	
С	.098	.138	2.50	3.50	
D	.228	.272	5.80	6.90	
Е	.344	.384	8.75	9.75	
F	.142	.165	3.60	4.20	
G	.512	.551	13.00	14.00	
Н	.093	.112	2.35	2.85	
- 1	.026	.037	0.65	0.95	
J	.012	.026	0.30	0.65	
K	.136	.160	3.45	4.05	
L	.169	.185	4.30	4.70	
М	.043	.059	1.10	1.50	
N	.087	.126	2.20	3.20	
0	.039	.055	1.00	1.40	

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ITO-220AB



DIMENSIONS					
DIM	INCHES		MILLIMETERS		NOTE
	MIN	MAX	MIN	MAX	NOTE
Α	.598	.638	15.20	16.20	
В	.386	.410	9.80	10.40	
С	.098	.138	2.50	3.50	
D	.232	.276	5.90	7.00	
Е	.344	.384	8.75	9.75	
F	.118	.142	3.00	3.60	
G	.472	.532	12.00	13.50	
Н	.093	.112	2.35	2.85	
ı	.026	.037	0.65	0.95	
J	.012	.026	0.30	0.65	
K	.124	.148	3.15	3.75	
L	.173	.189	4.40	4.80	
М	.091	.106	2.30	2.70	
N	.094	.134	2.40	3.40	
0	.039	.055	1.00	1.40	



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